

# FDR840P

## P-Channel 2.5V Specified PowerTrench® MOSFET

### General Description

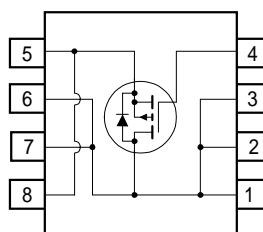
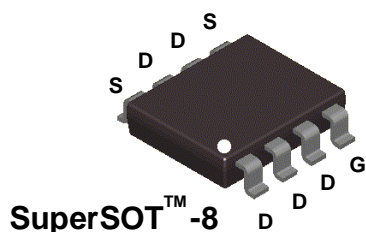
This P-Channel 2.5V specified MOSFET uses a rugged gate PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V – 12V).

### Applications

- Power management
- Load switch
- Battery protection

### Features

- -10 A, -20 V.  $R_{DS(ON)} = 12\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$   
 $R_{DS(ON)} = 17.5\text{ m}\Omega @ V_{GS} = -2.5\text{ V}$
- Fast switching speed.
- High performance trench technology for extremely low  $R_{DS(ON)}$
- High power and current handling capability



### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Rated	Units
V <sub>DSS</sub>	Drain-Source Voltage	-20	V
V <sub>GSS</sub>	Gate-Source Voltage	± 12	V
I <sub>D</sub>	Drain Current – Continuous (Note 1a)	-10	A
	– Pulsed	-50	
P <sub>D</sub>	Power Dissipation for Single Operation (Note 1a)	1.8	W
	(Note 1b)	1.0	
	(Note 1c)	0.9	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1a)	70	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case (Note 1)	20	°C/W

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDR840P	FDR840P	13"	12mm	2500 units

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-12		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage, Forward	$V_{GS} = 12\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate-Body Leakage, Reverse	$V_{GS} = -12\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

### On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.6	-0.8	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -8.4\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}, T_J = 125^\circ\text{C}$		10 14 13	12 17.5 18	m $\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-50			A
$g_{FS}$	Forward Transconductance	$V_{DS} = -10\text{ V}, I_D = -10\text{ A}$		49		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		4481		pF
$C_{oss}$	Output Capacitance			1532		pF
$C_{rss}$	Reverse Transfer Capacitance			540		pF

### Switching Characteristics (Note 2)

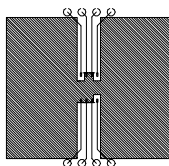
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -5\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$		15	30	ns
$t_r$	Turn-On Rise Time			15	30	ns
$t_{d(off)}$	Turn-Off Delay Time			120	240	ns
$t_f$	Turn-Off Fall Time			60	120	ns
$Q_g$	Total Gate Charge	$V_{DS} = -10\text{ V}, I_D = -10\text{ A},$ $V_{GS} = -4.5\text{ V}$		41	60	nC
$Q_{gs}$	Gate-Source Charge			6.4		nC
$Q_{gd}$	Gate-Drain Charge			11.8		nC

### Drain-Source Diode Characteristics and Maximum Ratings

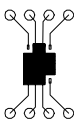
$I_S$	Maximum Continuous Drain-Source Diode Forward Current			-1.5		A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -1.5\text{ A}$ (Note 2)		-0.65	-1.2	V

#### Notes:

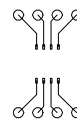
1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $70^\circ\text{W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper



b)  $125^\circ\text{W}$  when mounted on a  $.04\text{ in}^2$  pad of 2 oz copper



c)  $135^\circ\text{W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width <  $300\ \mu\text{s}$ , Duty Cycle < 2.0%

## Typical Characteristics

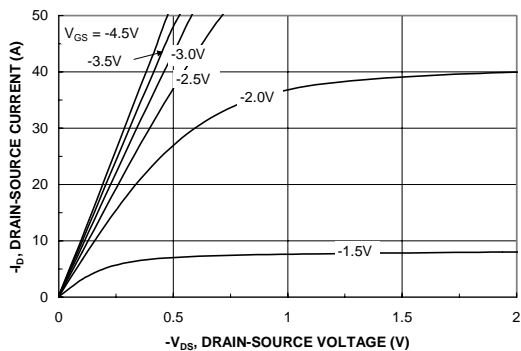


Figure 1. On-Region Characteristics.

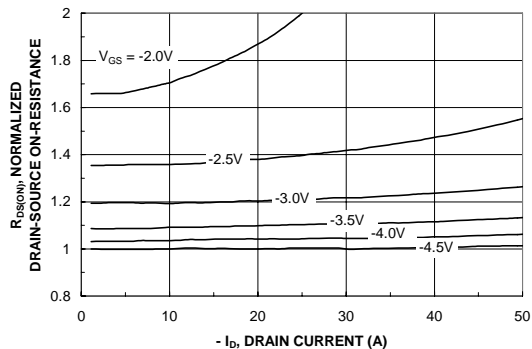


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

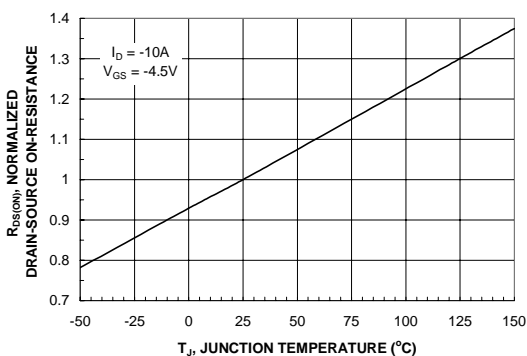


Figure 3. On-Resistance Variation with Temperature.

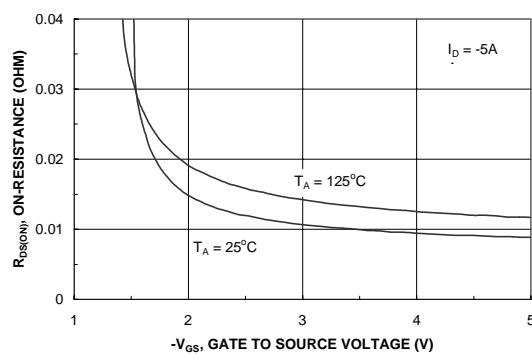


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

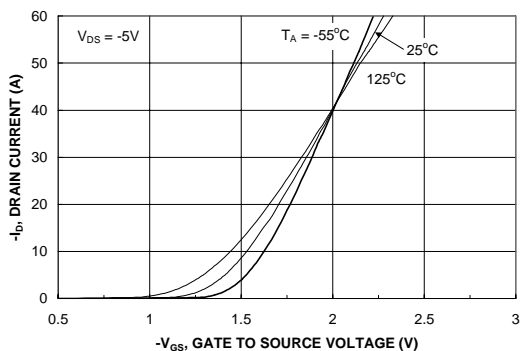


Figure 5. Transfer Characteristics.

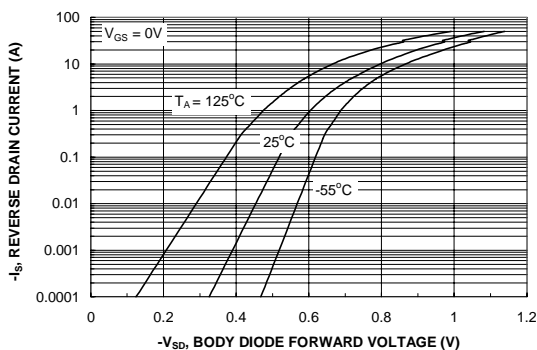


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics

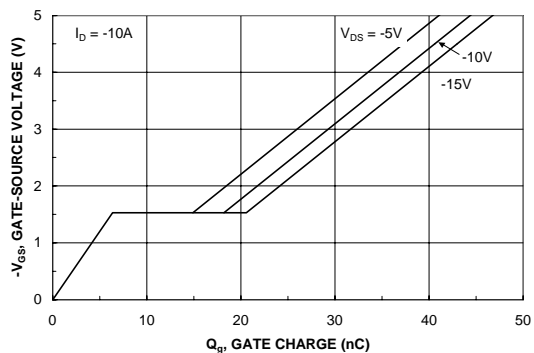


Figure 7. Gate Charge Characteristics.

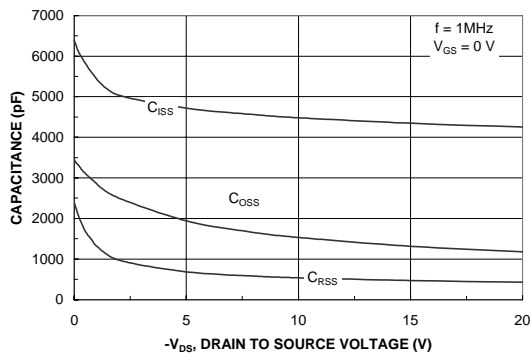


Figure 8. Capacitance Characteristics.

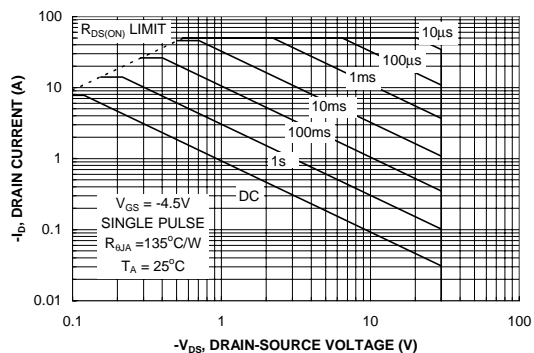


Figure 9. Maximum Safe Operating Area.

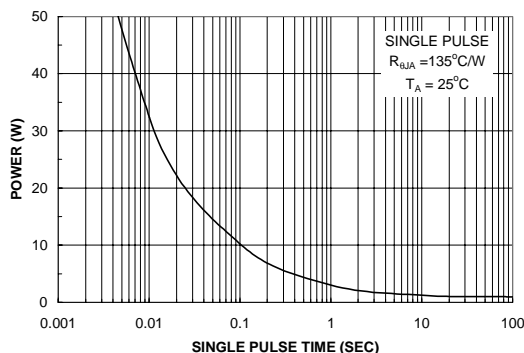


Figure 10. Single Pulse Maximum Power Dissipation.

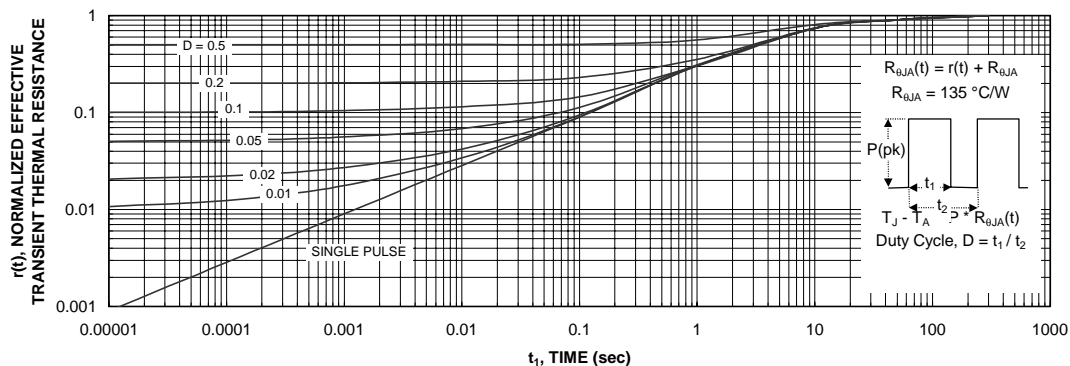


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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